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# A Fault Tolerant PMAD System Using Radiation Hardened Highly Integrated AFE Circuits

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# Agenda

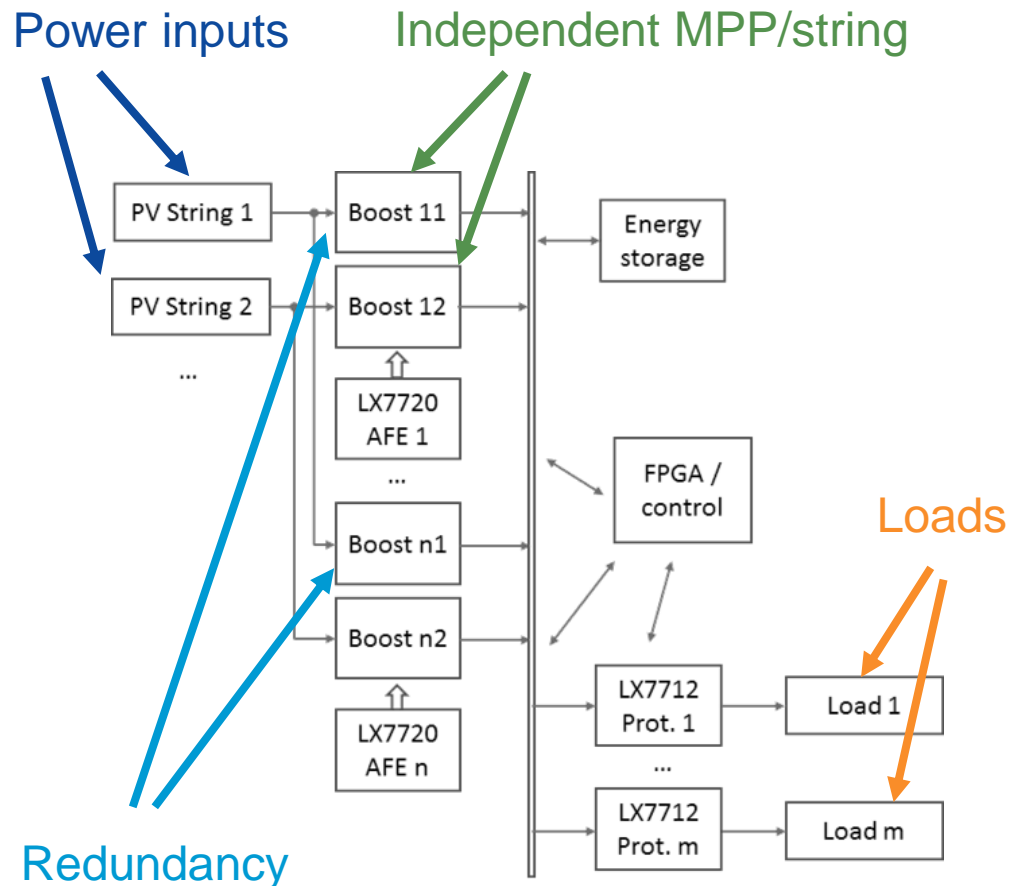
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- PMAD topology
- Fault Tolerant Power Stage
- LX7720 as analog front-end for DC/DC conversion
- LX7712 as power line protection for PMAD
- Control aspects

# PMAD Topology

## Power Management and Distribution

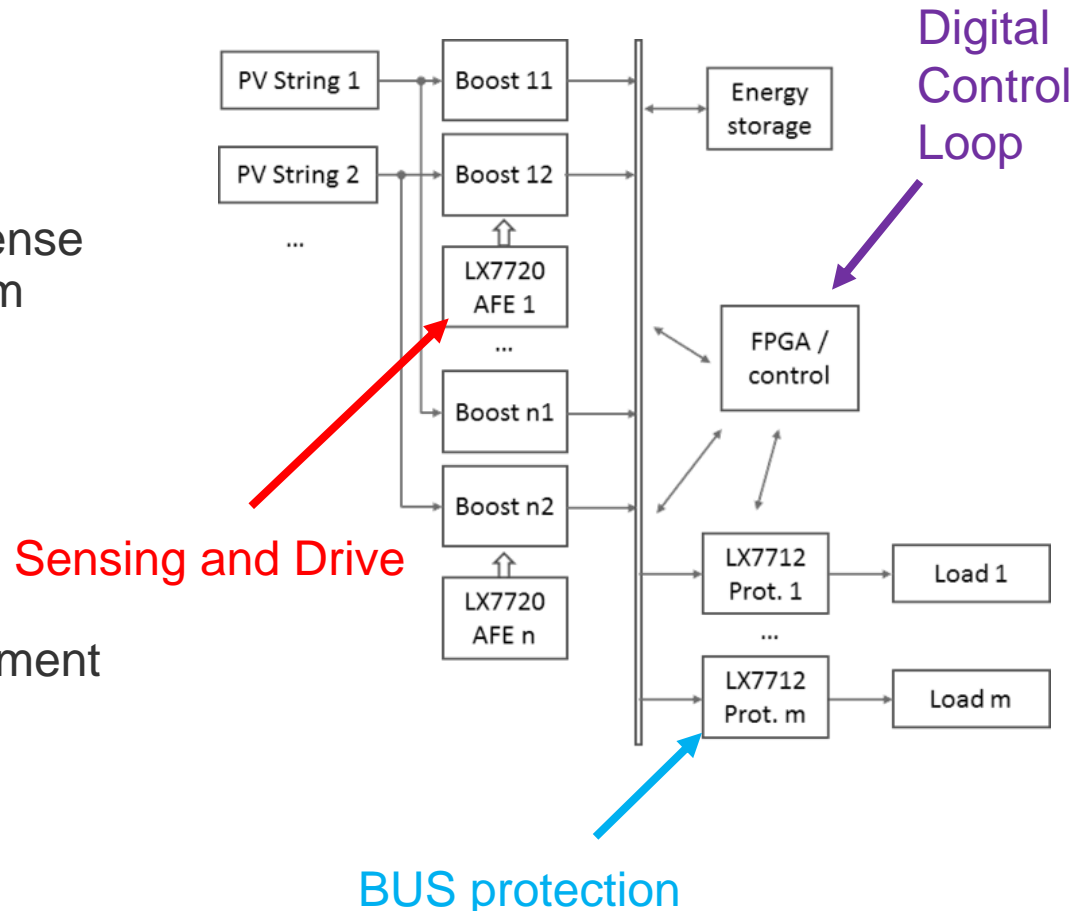
- Optimally transfers power from input sources, manages transmission of power to loads
- Consists of DC/DC converters, protection circuits, power transfer and fault management
- Inputs assumed as PV strings with fast MPPT control to track
  - Varying angle
  - Shading
  - Temperature per string



# PMAD Topology

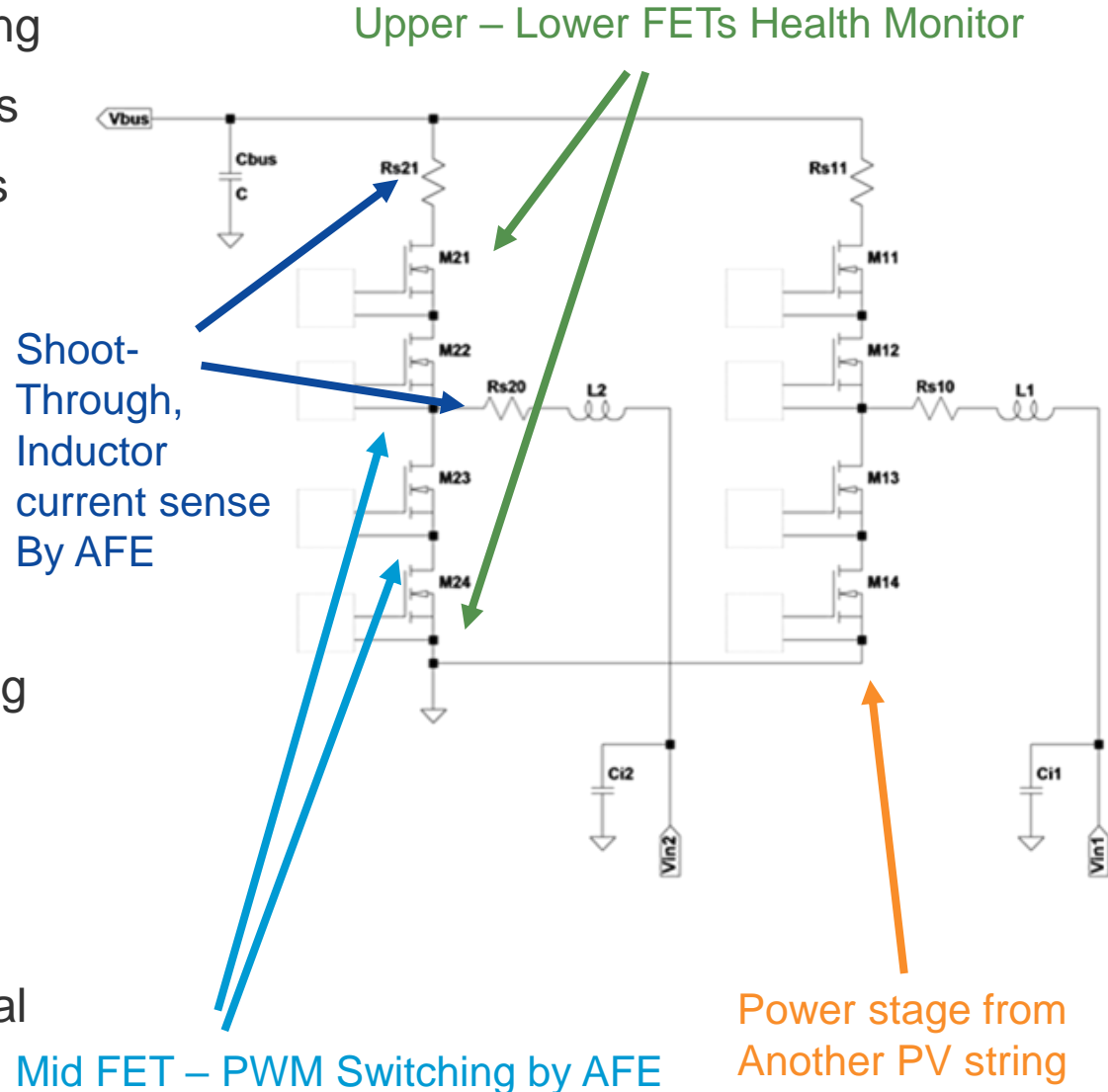
## Sensing, Drive and Control

- Voltages on input and output nodes and currents in each converter are sensed
- Loop control if done digitally
  - AFE converts to digital all sense lines + drives MOSFETs from PWM inputs
  - FPGA implements
    - DC/DC loop
    - MPPT
    - Power and safety management
- Power Distribution and Bus Protection implemented



# Power stage

- DC/DC units implemented using
  - 2 High-Side NMOS in series
  - 2 Low-Side NMOS in series
    - + Allows for FET short protection
    - - Efficiency penalty
- Regular switching Mid FETs – M22 M23
- Health Monitoring by exercising upper and Lower FETs – M21 and M24
- Shoot through current or inductor current detect to signal Fault



# Power stage fault simulation

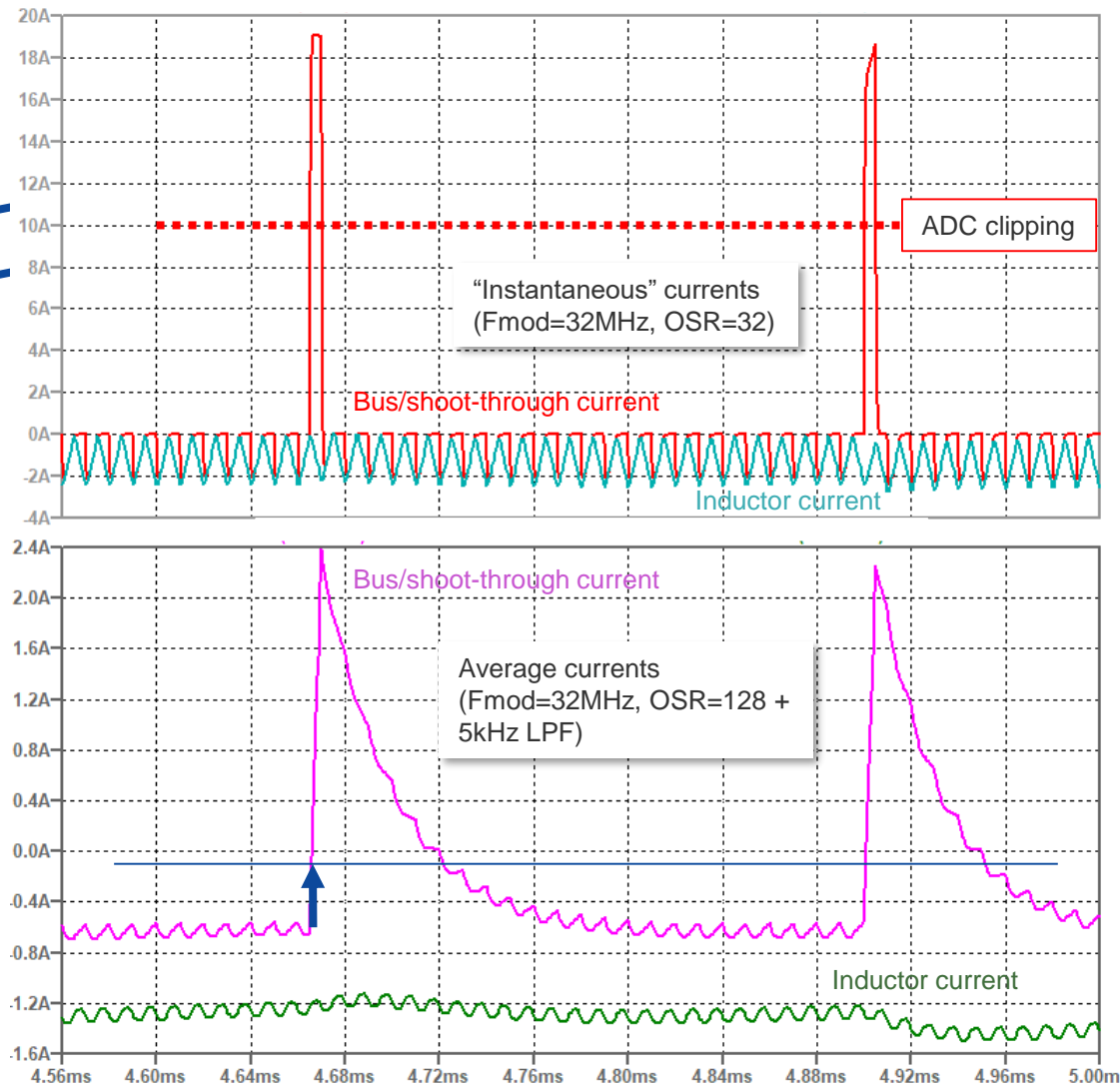
- Fault detect waveforms with 5 Ohms faults

- on M14/M24
- on M11/M21

- Criteria in this case:

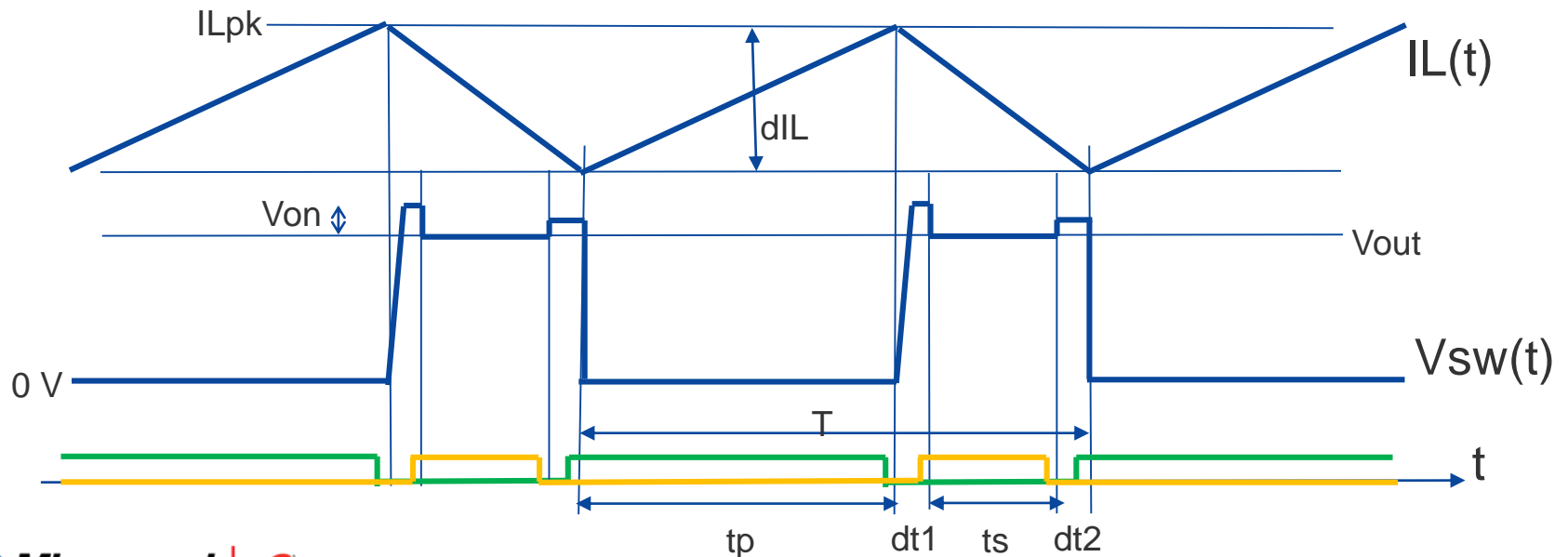
“If the change in average current during the test switching cycle is higher than 0.5A then tested device is developing a short.”

Note: Inductor current is almost unaffected (same for output and input voltages)



# Dead time simple model

- For Synchronous Boost in CCM: if  $dt1$  and  $dt2$  are too large they impact efficiency so  $dt1,2$  should be minimized.
- If  $dt1$  and  $dt2$  are negative then a large shoot through current will reduce efficiency
- There is a maximum efficiency point



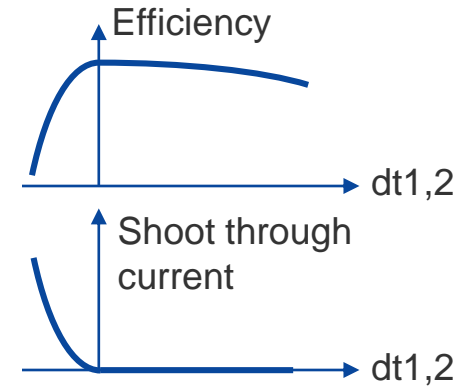
# Dead time simple model cont.

- For  $dt > 0$  degradation is sub percent for 100V output.
- Efficiency degrades most when  $dt$  is negative (there is shoot through current).

$$\eta \approx 1 - \frac{V_{out}^2 / R_{short}}{V_{out}^2 / R_{load} T} |dt| = 1 - \frac{|dt|}{T} \times \frac{R_{load}}{R_{short}}$$

For example for  $dt = -1\text{ns}$ ,  $T = 10\mu\text{s}$ ,  $R_{load} = 300\Omega$ ,  $R_{short} = 0.3\Omega \Rightarrow 1 - \eta = 10\%$

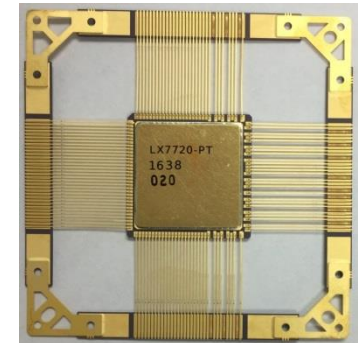
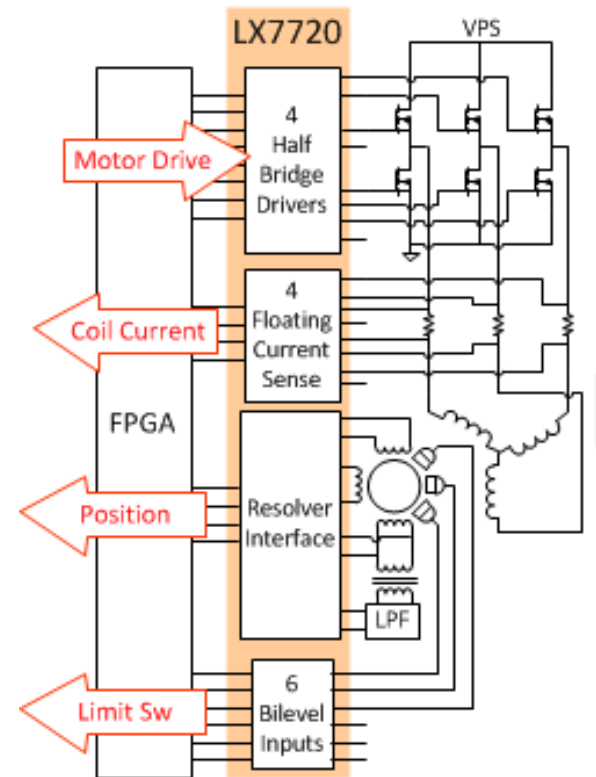
- Traditional design: dead time is insured based on margining worst case delays + jitter between driver chain for each MOSFET
- Our topology can sense the effect of dead time drift due to temperature, aging or radiation so it can continuously optimize efficiency and keep  $dt$  minimum





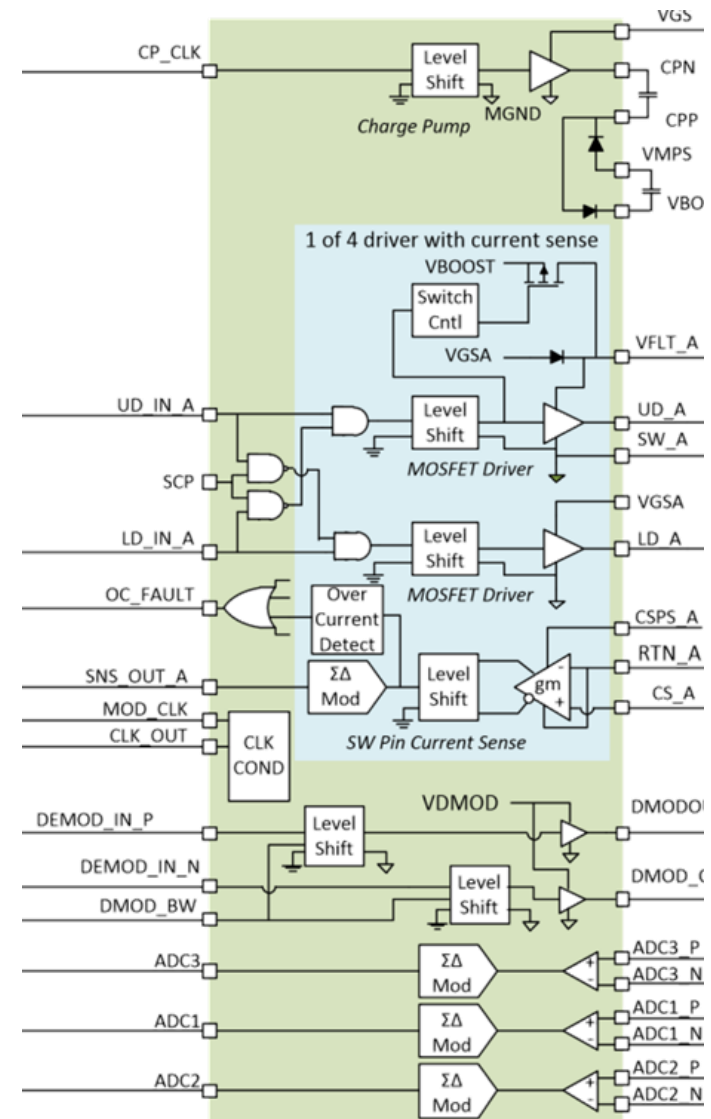
# LX7720 Power Driver with Current Sensing Highlights and Applications

- Space System Manager – Motor Control – Power Management
- Motor driver Servo Control
- Linear actuator servo control
- Stepper, BLDC, PMSM motor driver
- DC/DC
- Power drivers up to 150V
- In-line Current Sense with embedded converters
- 132-lead ceramic Quad Flat Pack package - 24mmx24mm



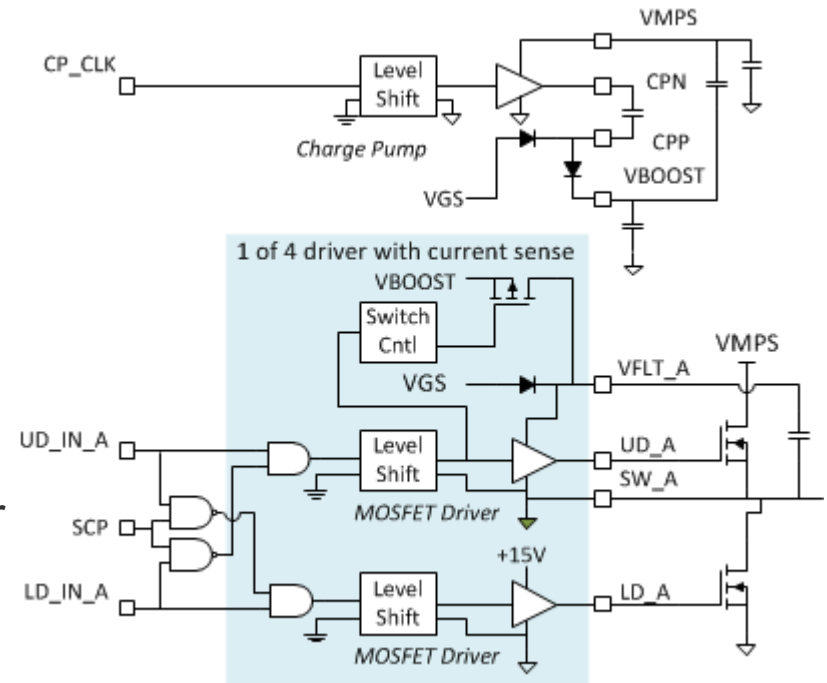
# LX7720 Power Driver with Current Sensing Features

- Four Half-Bridge Nch MOSFET drivers
- Four floating differential current sensors with  $\Sigma\Delta$  modulated processed outputs to FPGA
- Pulse density modulated resolver exciter
- Three differential resolver sensors with  $\Sigma\Delta$  modulated processed outputs to FPGA
- Six threshold configurable logic inputs
- Ground isolation signal-to-motor
- Six bi-level logic inputs
- Fault detection
- Radiation Tolerant
  - SEL free – 87Mev-cm<sup>2</sup>/mg
  - 100krad TID
  - ELDRS tested up to 50krads



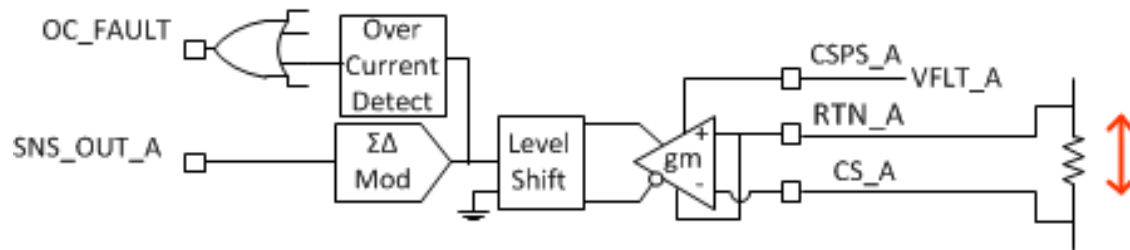
# LX7720 Power Drivers

- There are 4 half bridge drivers
- Upper driver is floating N ch MOSFET
- Supports power rails up to 150V
- Switching frequency to 200kHz
- Supports 100% duty cycle for upper or lower switches.
- Bootstrap option for powering upper driver also supported
- Long term shoot through prevention



# LX7720 Floating Current Sense

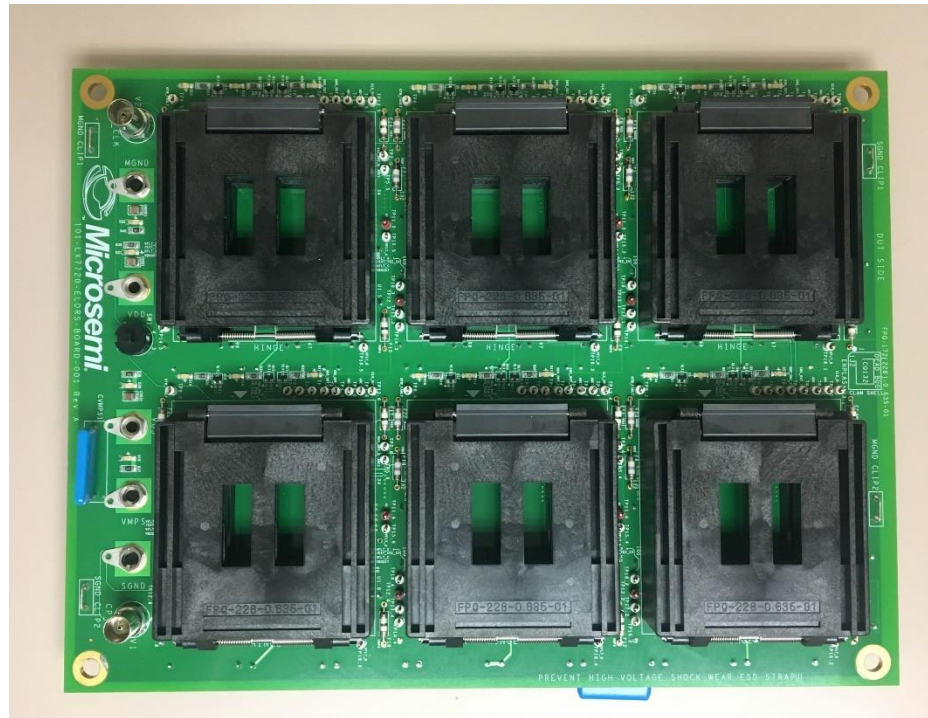
- Capable of sensing current at the switch pin; this gives a true indication of coil current.
- Senses a +/-250mV differential analog signal. Rejects a common mode signal of 150Vpk changing at a rate of 15KV/us.
- Single line sigma delta data stream output to FPGA
- 2<sup>nd</sup> order sigma delta modulator at 32MHz
- Provides OC fault detection for levels exceeding 300mV



*Floating Current Sense*

# LX7720 Radiation testing schedule

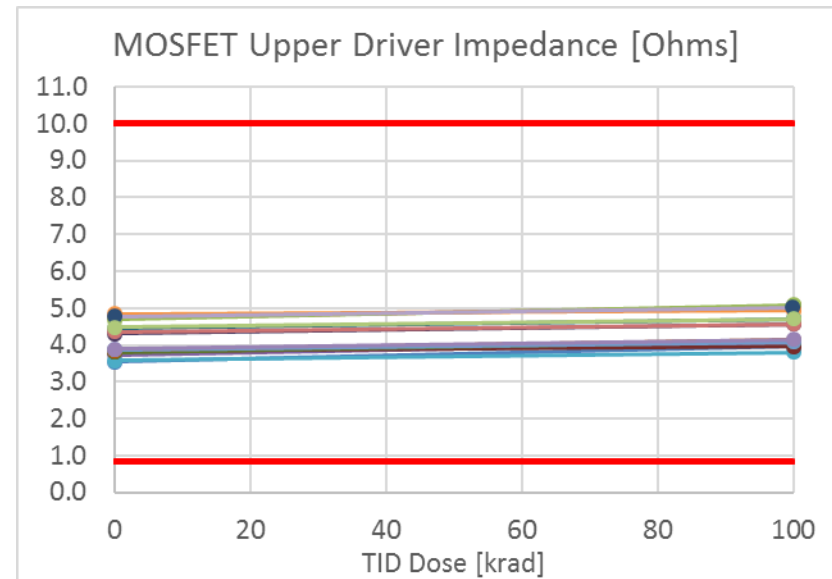
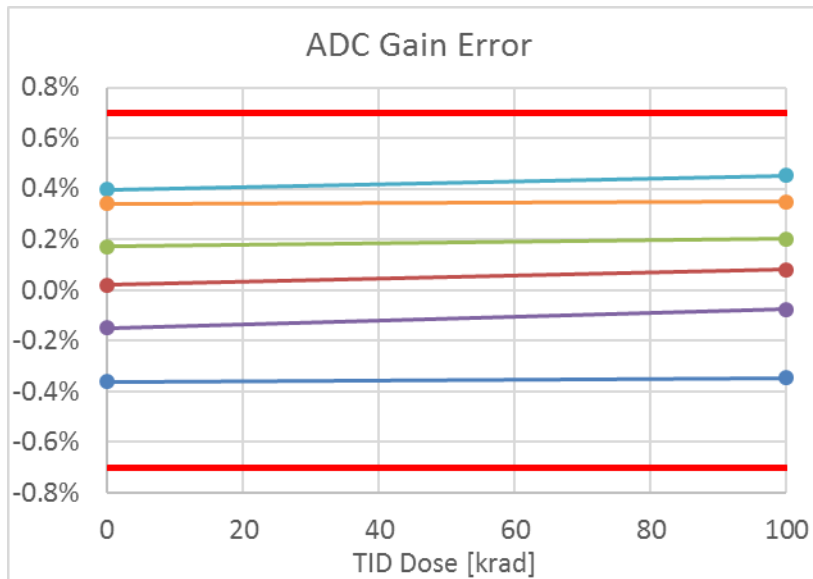
- Preliminary 100krad test performed at DMEA in May 2018
- Final 100krad test under way. Data will be presented at NSREC
- 100krad test of qual lot to be completed in November 2018
- 50krad ELDRS to be completed in February 2019
- SEE testing scheduled for end of June, data will be presented at RADECS



# LX7720 TID 100krad

## ■ Preliminary 100krad results:

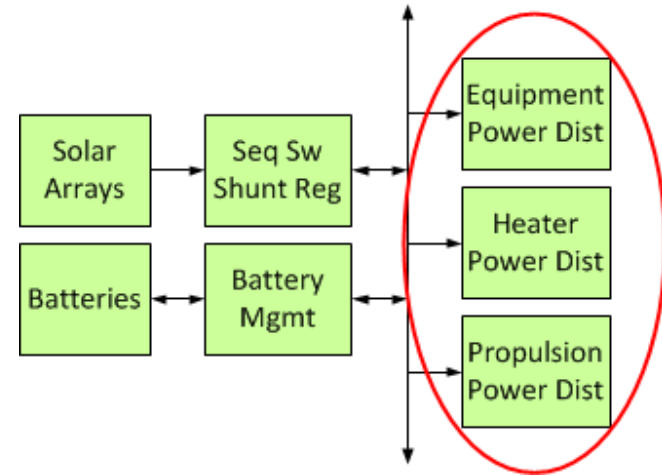
- No significant shifts observed on the following parameters:
  - Current consumption
  - Reference voltage
  - Fault thresholds
  - Bi-level inputs and logic I/O parameters
  - ADC gain
- Small increase, 5-10%, in the MOSFET and DMOD drivers impedance
- Small degradation of ADC offset ( $<0.15\%$ FSR)



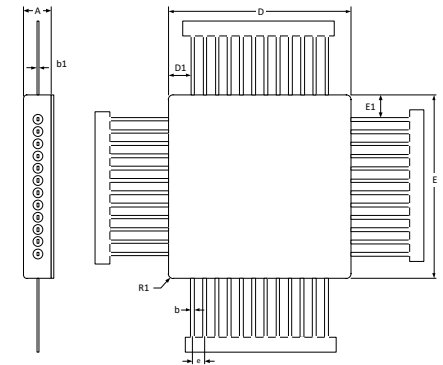
# LX7712 Power Line Protector Device

## Highlights and Applications

- Used for power control and distribution
- Provides a protected integrated switch
- Turns on and off DC load with current of up to 5A
- Latch-able current limit protection
- Fold-back current limit protection
- Can be paralleled for higher currents
- 48-lead hermetic HTF flatpack package - 19mmx19mm



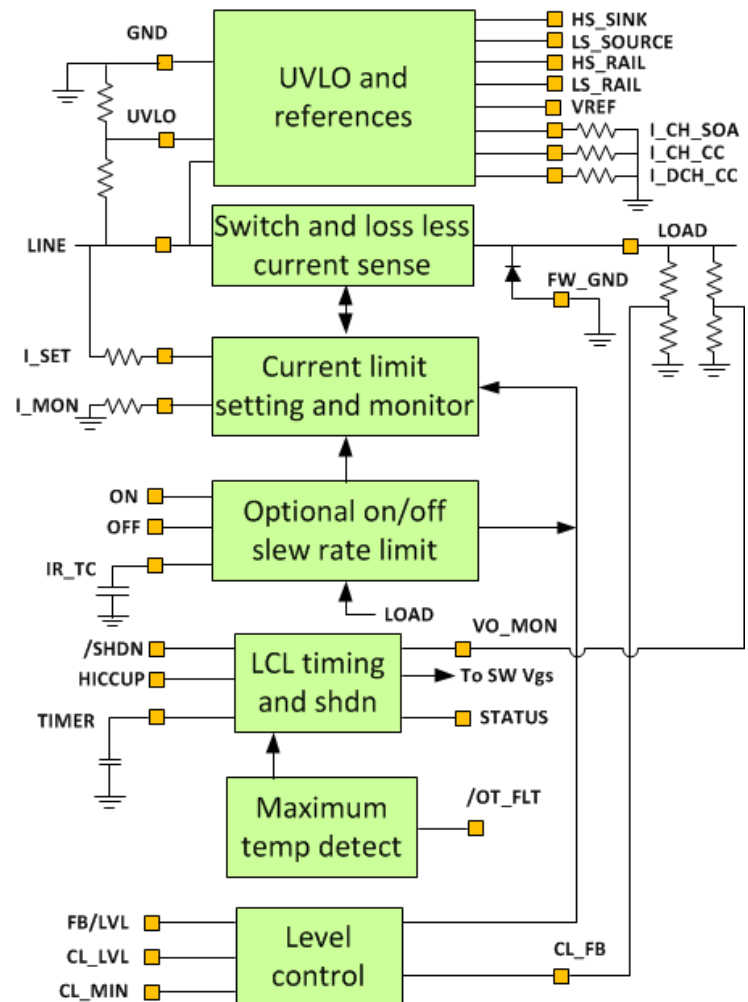
- ESA Standards:
  - ECSS-E-HB-20-20A: Electrical design and interface requirements for power supply
  - ECSS-E-ST-20-20C: Guidelines for electrical design and interface requirements for power supply



# LX7712 Power Line Protector Device

## Features

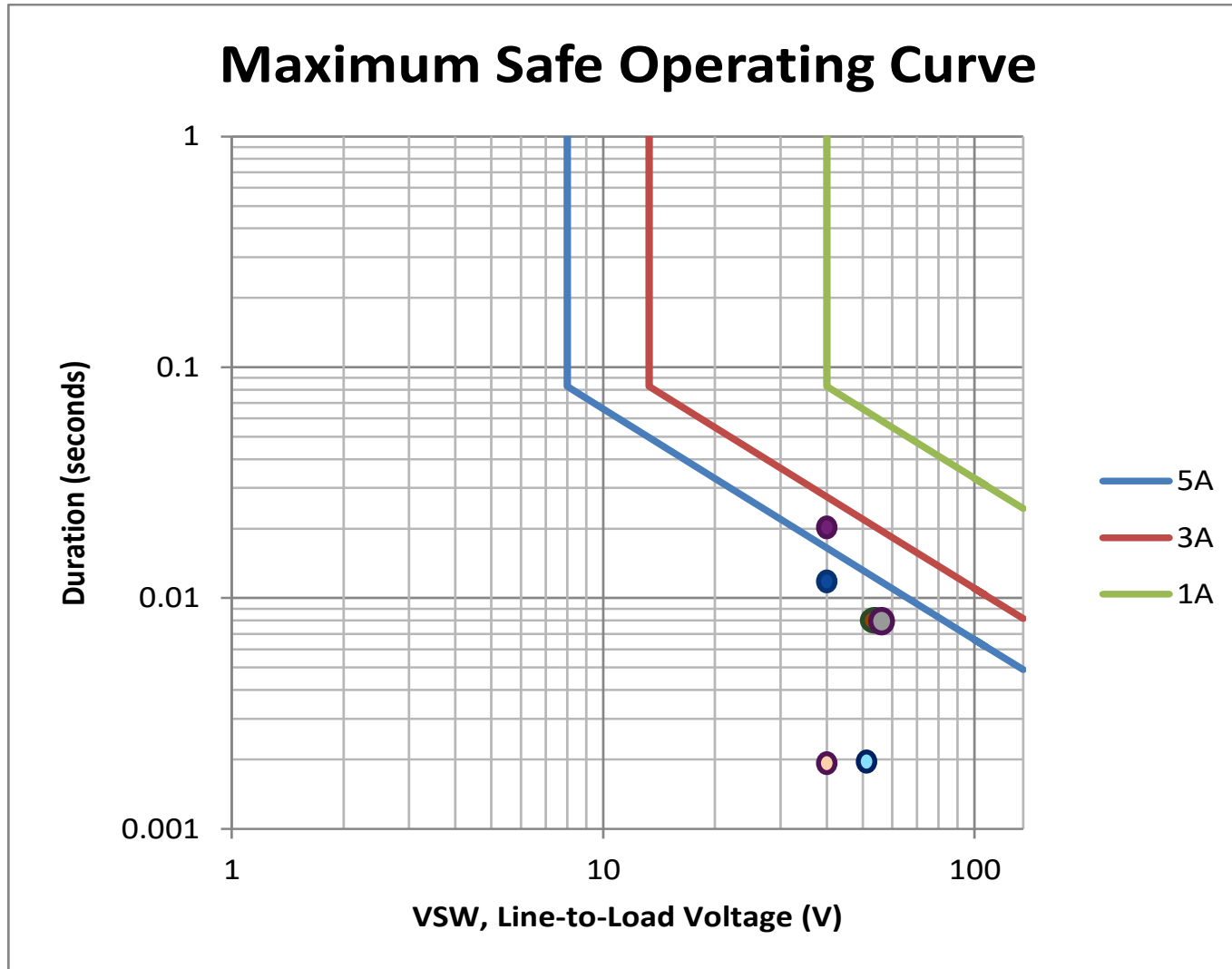
- Internal 5A PMOS switch and catch diode
- 120V rated
- LCL or FCL configurable
- ON, OFF, and STATUS pins
- Programmable UVLO and current levels
- Current monitor output
- Current slew rate control: on and off
- Programmable timer
- Optional hiccup restart mode
- Temperature shutdown - optional
- Radiation Tolerant
  - SEL free – 87Mev-cm<sup>2</sup>/mg
  - 100krad TID
  - ELDRS tested up to 50krads





# LX7712 Power Line Protector Device

## Classification as LCL, HLCL & RLCL



#### LEGEND:

- RLCL 2B (38V, 2.2-2.8A, 10-20ms)
- RLCL 2 (52V, 2.2-2.8A, 4-8ms)
- LCL 4 (38V, 4.4-5.6A, 6-12ms)
- LCL 4B (52V, 4.4-5.6A, 4-8ms)
- HLCL 4 (38V, 4.4-5.6A, 0.5-2ms)
- HLCL 4 (52V, 4.4-5.6A, 0.5-2ms)

Note: for LCL and HLCL classification the max current limit needs to be set between 4.4-5A for LX7712

# DC/DC control

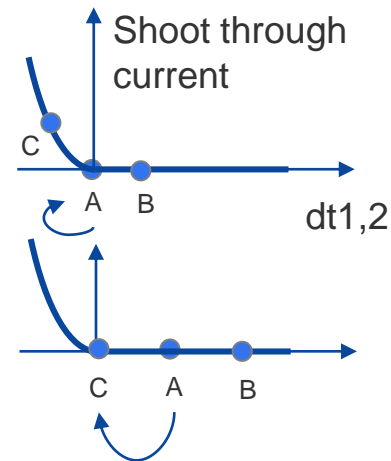
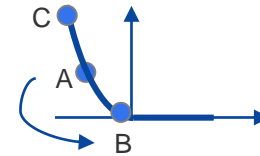
- Fast loop / slow loop approach
  - Fast loop implements a PID controller for each of the two boost DC/DC converters served by each LX7720
    - PID controller at switching frequency regulates voltage across the input PV string to a target voltage by controlling the duty cycle, bandwidth 5-10x switching frequency.
    - Power stage SOA sensing can overwrite the target
  - Slow loop is an integral controller updating the target voltage of the fast loop in order to optimize the input power (MPPT), bandwidth 100x switching frequency (1kHz)
    - Simple “perturb and observe” or more complex (see paper references)

# Dead time control

- Dead time (dt) optimization (and redundant fault monitoring) is running at a much slower pace than slow loop (e.g. 1Hz)
- Optimization based on perturb and observe method using the fact that the only observable degradation is at negative dt.

## 1. Start from A and test B and C

- If  $C \gg A \approx B$  stay in A
- If  $C \gg A \gg B$  move to B
- If  $C \approx A \approx B$  move to C
- If  $C < A$  or  $A < B$  error, set conservative dt

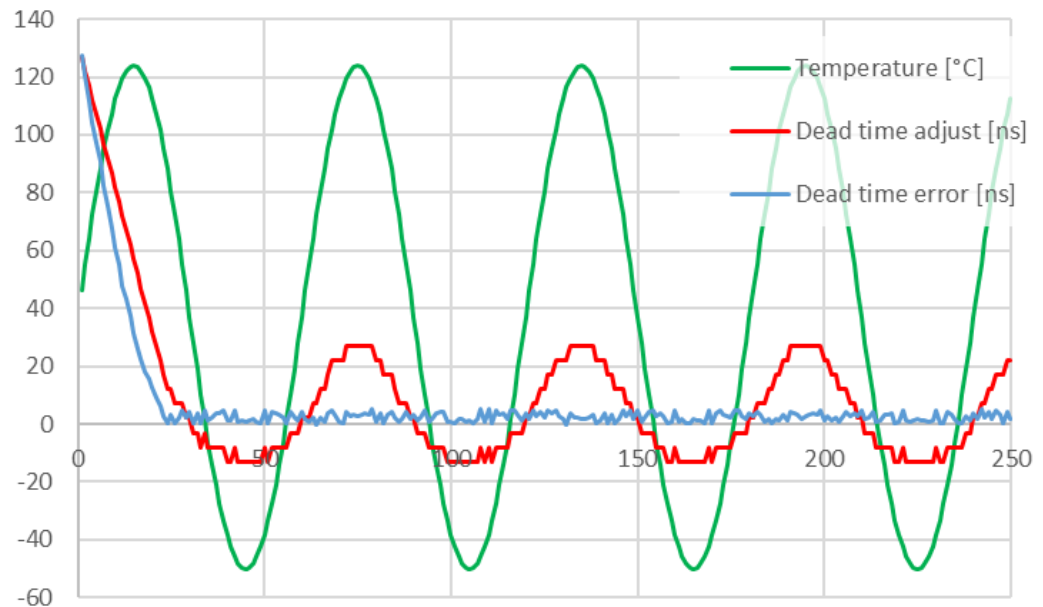


## 2. Repeat 1.

# Dead time loop modeling

- Modeled dead time adjustment control and a delay mismatch temperature model to verify operation.
- Simulation: response to thermal cycles.

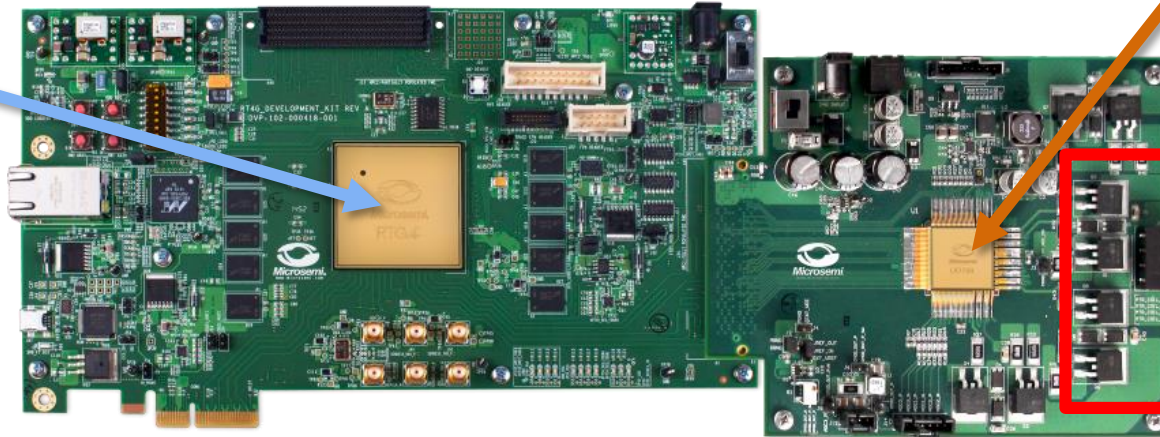
- Dead time adjustments are done at the level of the PWMs driving the higher and lower MOSFETs
- PWM delay resolution is 5ns
- Dead time adjust is the extra delay added to the nominal rising edge of the upper MOSFET gate driver.
- Dead time error is the difference between ideal dead time adjust and current dead time
- Initial safe dead time adjustment is 125ns



# Experimental data

- LX7720 motor control evaluation

FPGA

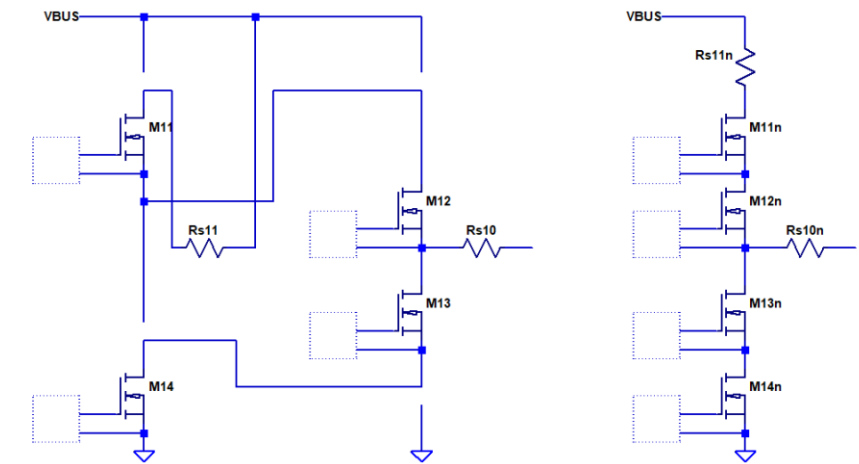


LX7720

4MOSFETs  
to emulate  
new power  
stage

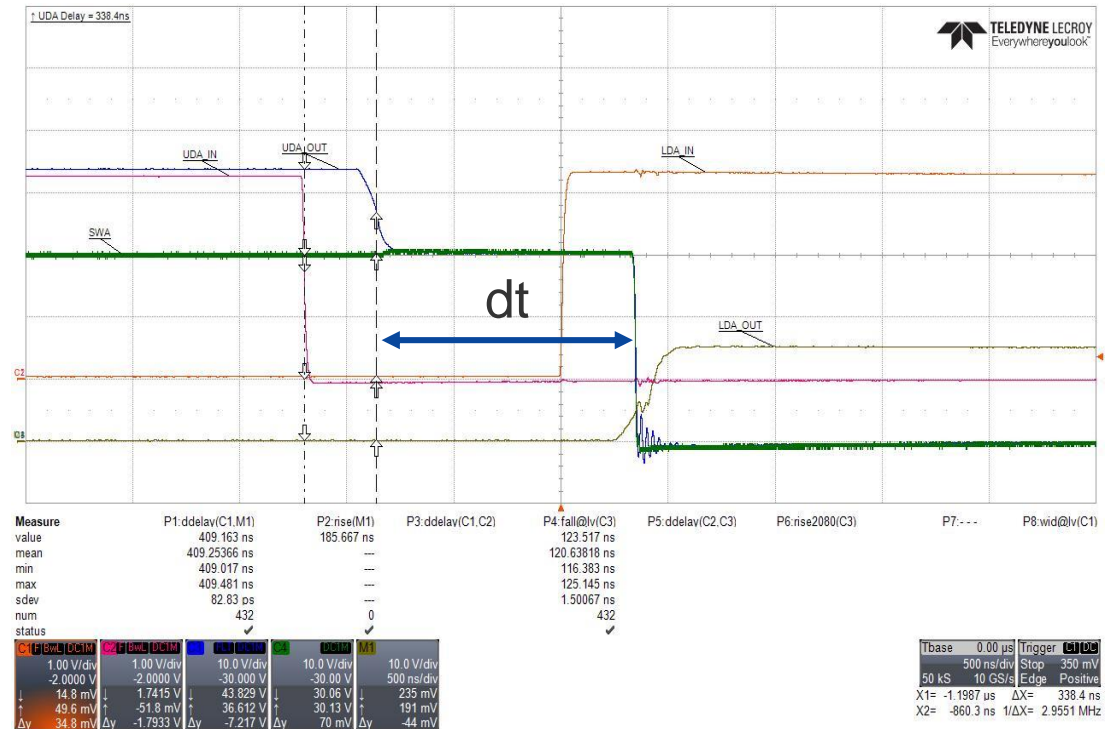
- Modification to evaluate the new power stage

Two half bridge circuits  
reconnected



# Experimental data cont.

- In a conservative design to margin for TID and temperature variation of the 7720 and MOSFETs  $dt$  is set to 1.2 $\mu$ s.
  - If we want duty cycle up to 10% then  $dt$  margin is maximum 5%  $\Rightarrow T_{sw} = 24\mu$ s
  - If we use  $dt$  control with a step of 5ns then  $dt$  becomes negligible
  - the new limiting factor will be the gate driver minimum pulse width ( $\sim 500$ ns) and  $T_{sw} = 5\mu$ s.
- $\Rightarrow$  5x higher switching frequency possible with  $dt$  control.



# Conclusions and future work

- In this presentation we have shown:
  - A new PMAD topology
  - A 4-MOSFET Fault Tolerant Power Stage
  - How to use LX7720 as analog front-end for DC/DC conversion using the fault tolerant power stage
  - How to apply LX7712 as power line protection for this particular PMAD
  - Details of the system control aspects:
    - How to detect faults and switch to redundant system
    - How to constantly optimize deadtime and be tolerant to parametric shift of MOSFET control delay

# Conclusions and future work

- Future integration in an application/evaluation board once the LX7712 is available.
- System verification:
  - Emulate
    - loads and load faults using programmable loads
    - sources by using a PV simulator
  - Use an NI box to control the sources and loads and measure performance, behavior and fault tolerance





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